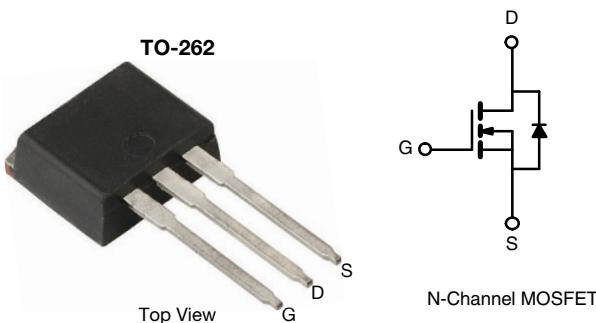


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	60
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00470
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.00600
I _D (A)	120
Configuration	Single
Package	TO-262

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	T _C = 25 °C ^a	I _D	120	A
	T _C = 125 °C		91	
Continuous Source Current (Diode Conduction) ^a		I _S	120	
Pulsed Drain Current ^b		I _{DM}	300	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	80	mJ
Single Pulse Avalanche Energy		E _{AS}	320	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	250	W
	T _C = 125 °C		83	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)		R _{thJC}	0.6	

Notes

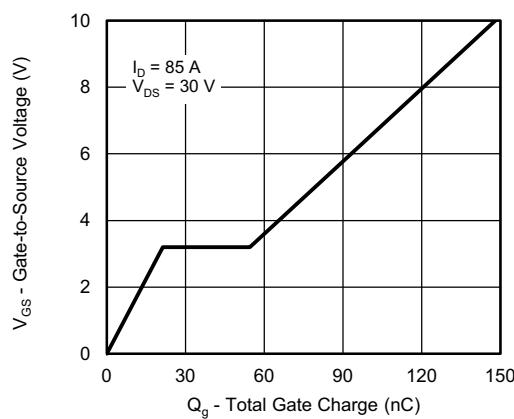
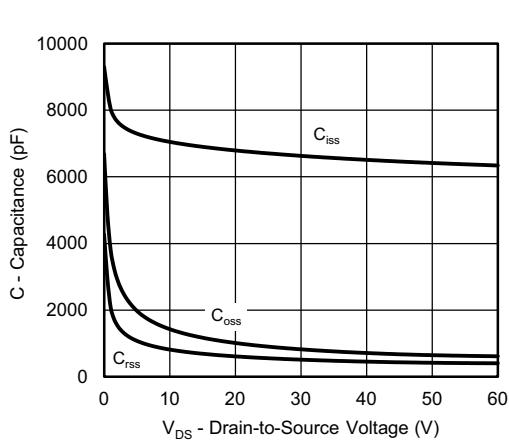
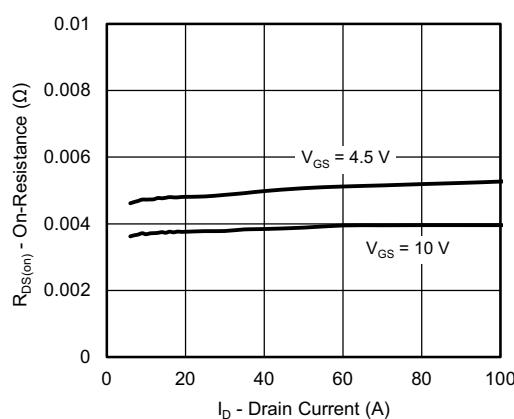
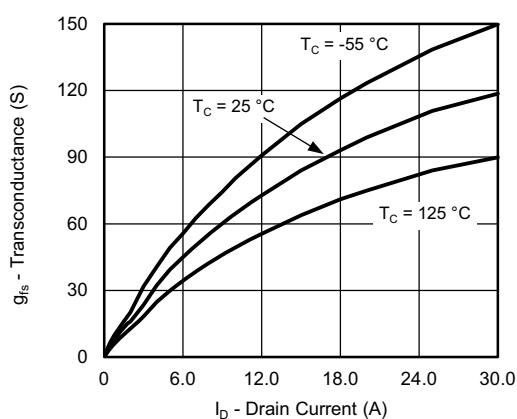
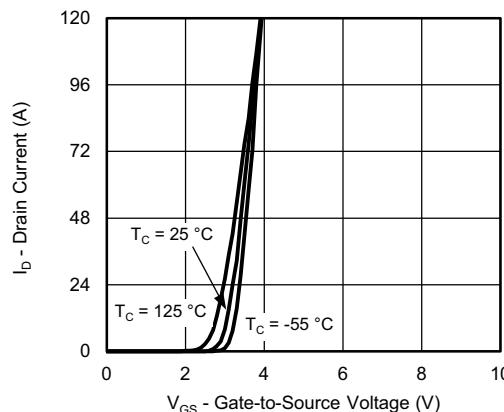
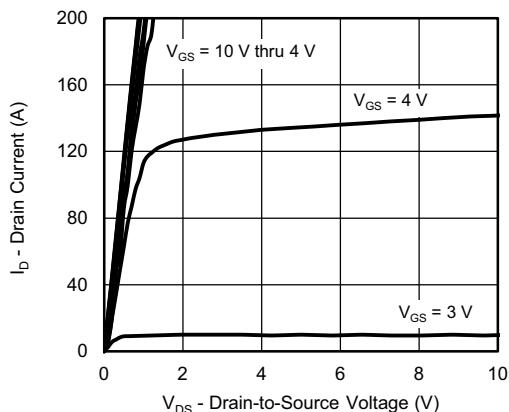
- Package limited.
- Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.

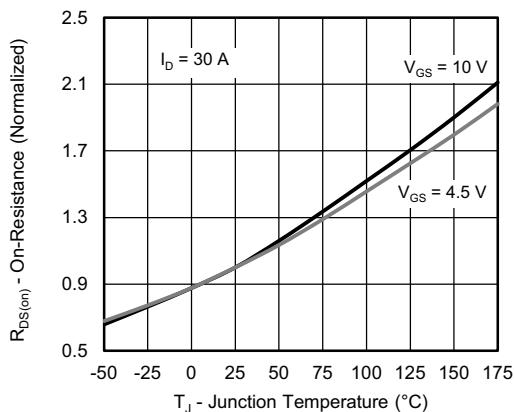
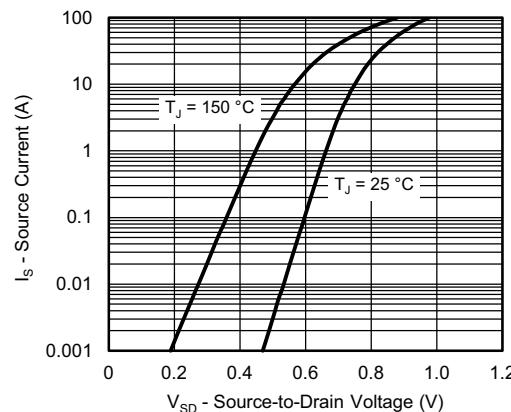
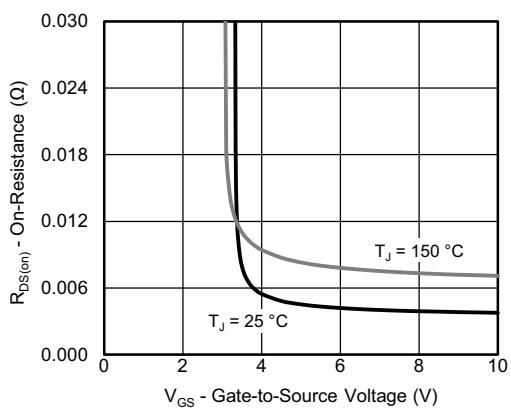
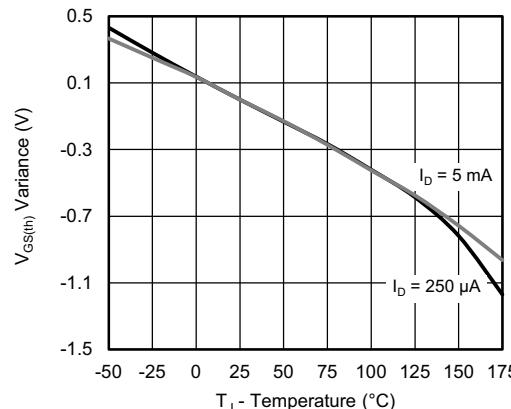
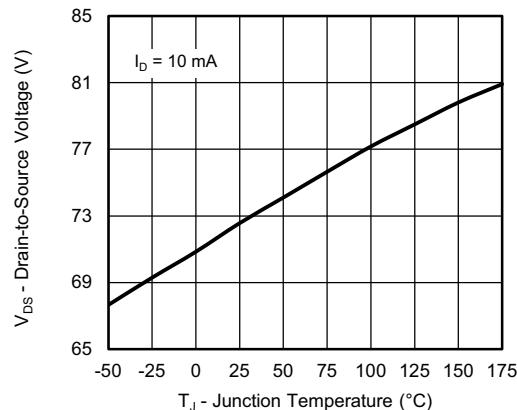
SPECIFICATIONS ($T_C = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		1.5	2.0	2.5		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$	-	-	1	μA	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$, $T_J = 125^\circ\text{C}$	-	-	50		
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 60 \text{ V}$, $T_J = 175^\circ\text{C}$	-	-	500		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{GS} = 10 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	120	-	-	A	
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$	$I_D = 30 \text{ A}$	-	0.00378	0.00470	Ω	
		$V_{GS} = 10 \text{ V}$	$I_D = 30 \text{ A}$, $T_J = 125^\circ\text{C}$	-	-	0.00801		
		$V_{GS} = 10 \text{ V}$	$I_D = 30 \text{ A}$, $T_J = 175^\circ\text{C}$	-	-	0.00992		
		$V_{GS} = 4.5 \text{ V}$	$I_D = 20 \text{ A}$	-	0.00481	0.00600		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 30 \text{ A}$		-	118	-	S	
Dynamic ^b								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	-	6705	8800	pF	
Output Capacitance	C_{oss}			-	904	1200		
Reverse Transfer Capacitance	C_{rss}			-	555	800		
Total Gate Charge ^c	Q_g	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}$, $I_D = 85 \text{ A}$	-	148	230	nC	
Gate-Source Charge ^c	Q_{gs}			-	21.4	-		
Gate-Drain Charge ^c	Q_{gd}			-	33.2	-		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		0.45	0.99	1.5	Ω	
Turn-On Delay Time ^c	$t_{d(\text{on})}$	$V_{DD} = 30 \text{ V}$, $R_L = 0.353 \Omega$ $I_D \approx 85 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		-	16	25	ns	
Rise Time ^c	t_r			-	9	15		
Turn-Off Delay Time ^c	$t_{d(\text{off})}$			-	46	75		
Fall Time ^c	t_f			-	12	20		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I_{SM}			-	-	300	A	
Forward Voltage	V_{SD}	$I_F = 70 \text{ A}$, $V_{GS} = 0$		-	0.92	1.5	V	

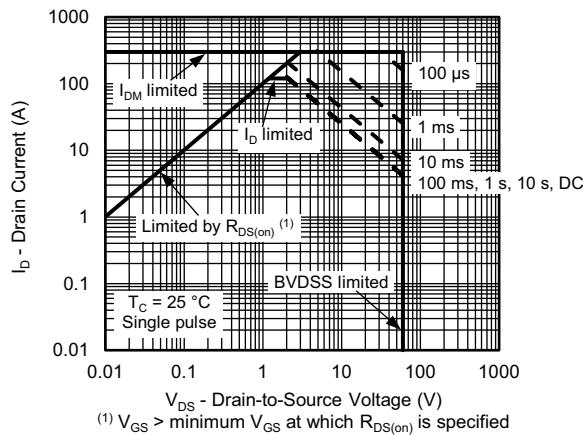
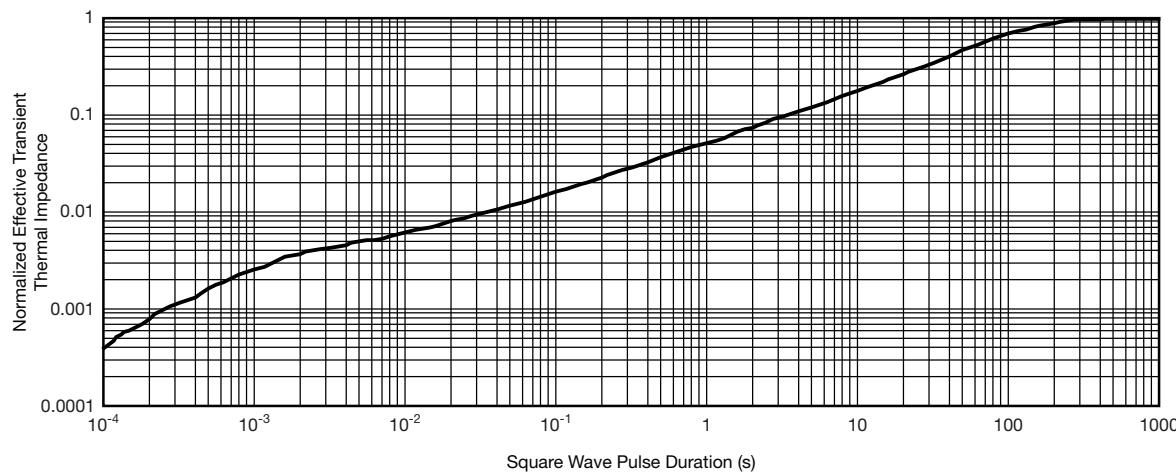
Notes

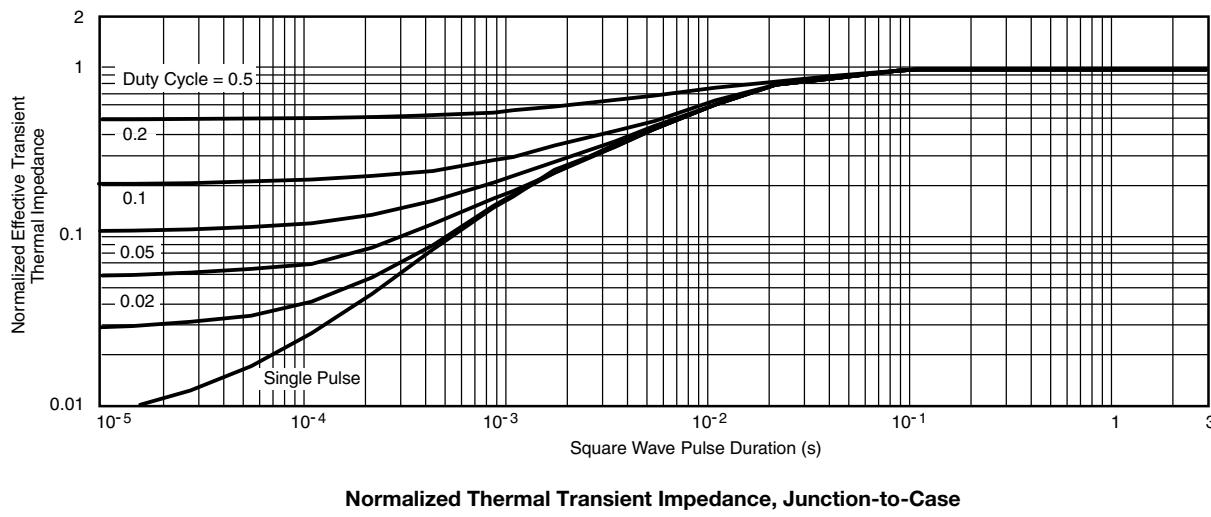
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

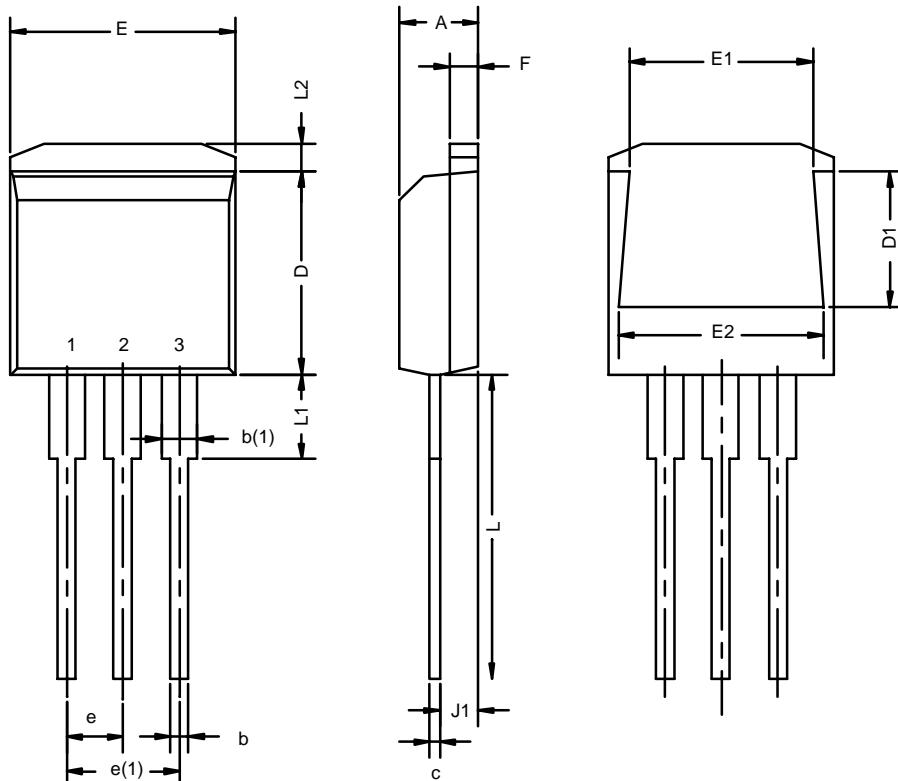
THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25°C)
 - Normalized Transient Thermal Impedance Junction to Case (25°C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?266962.

TO-262: 3-LEAD


Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055

ECN: T-02234—Rev. C, 14-Oct-02
DWG: 5855

*Use millimeters as the primary measurement



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- Поставка более 17-ти миллионов наименований электронных компонентов;
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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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